

**SOT-23 Formed SMD Package**

**CSA1162**

*LOW FREQUENCY GENERAL PURPOSE AMPLIFIER TRANSISTOR*

*P-N-P transistor*

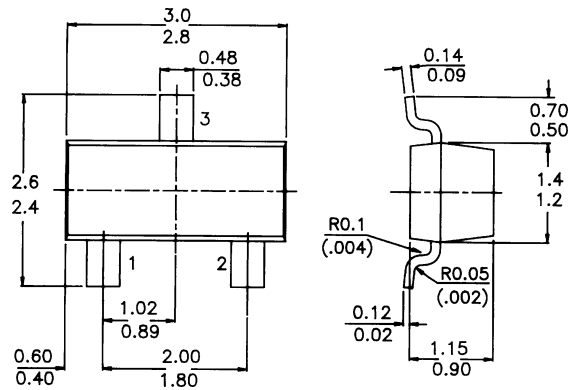
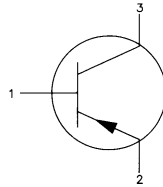
**Marking**

CSA1162Y-3E  
CSA1162GR(G)-3F

*PACKAGE OUTLINE DETAILS  
ALL DIMENSIONS IN mm*

**Pin configuration**

- 1 = BASE
- 2 = EMITTER
- 3 = COLLECTOR



**ABSOLUTE MAXIMUM RATINGS**

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	50 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	50 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	150 mA
Total power dissipation at $T_{amb} = 25^\circ C$	$P_{tot}$	max.	150 mW
Junction temperature	$T_j$	max.	150 °C
D.C. current gain	$h_{FE}$	min.	70
$-I_C = 2 \text{ mA}; -V_{CE} = 6V$		max.	400

**RATINGS (at  $T_A = 25^\circ C$  unless otherwise specified)**

<i>Limiting values</i>			
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	50 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	50 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	150 mA
Base current	$-I_B$	max.	30 mA

Total power dissipation at $T_{amb} = 25^{\circ}C$	$P_{tot}$	max.	150 mW
Storage temperature	$T_{stg}$	-50 to +150	$^{\circ}C$
Junction temperature	$T_j$	max.	150 $^{\circ}C$

**CHARACTERISTICS** (at  $T_A = 25^{\circ}C$  unless otherwise specified)

## Collector-emitter breakdown voltage

$-I_C = 1 \text{ mA}; I_B = 0$	$-V_{(BR)CEO}$	min.	50 V
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## Collector cut-off current

$-V_{CB} = 50 \text{ V}; I_E = 0$	$-I_{CBO}$	max.	100 nA
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## Emitter cut-off current

$V_{EB} = 5 \text{ V}; I_C = 0$	$I_{EBO}$	max.	100 nA
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## Saturation voltage

$-I_C = 100 \text{ mA}; -I_B = 10 \text{ mA}$	$-V_{CEsat}$	max.	0.3 V
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## D.C. current gain

$I_C = 2 \text{ mA}; -V_{CE} = 6 \text{ V}$	$h_{FE}$	min.	70
		max.	400
	$Y$	min.	120
		max.	240
	$GR(G)$	min.	200
		max.	400

## Transition frequency

$V_{CE} = 10 \text{ V}; I_C = 1 \text{ mA}$	$f_T$	min.	80 MHz
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## Collector output capacitance

$V_{CB} = 10 \text{ V}; I_E = 0; f = 1 \text{ MHz}$	$C_{ob}$	max.	7 pF
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## Noise figure

$V_{CE} = 6 \text{ V}; I_C = 0.1 \text{ mA}$ $f = 1 \text{ kHz}; R_g = 10 \text{ k}\Omega$	$N_F$	max.	10 dB
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### Disclaimer

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